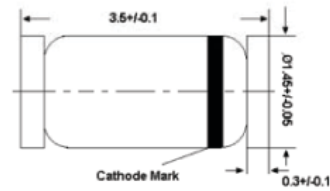


## Silicon Epitaxial Planar Switching Diode

### Features

- Fast switching speed
- High reliability
- High conductance
- For general purpose switching applications

LL-34



Glass case MinIMELF  
Dimensions in mm

### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	$V_{RM}$	50	V
Average Rectified Forward Current	$I_{F(AV)}$	200	mA
Forward Continuous Current	$I_{FM}$	300	mA
Power Dissipation	$P_{tot}$	500	mW
Junction temperature	$T_j$	175	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 65 to +175	$^\circ\text{C}$

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 200\text{ mA}$	$V_F$	1.2	V
Reverse Current at $V_R = 50\text{ V}$	$I_R$	100	nA
Reverse Recovery Time at $I_F = I_R = 10\text{ to }200\text{ mA}$ , to $0.1 I_F$	$t_{rr}$	4	ns